

DESCRIPTION

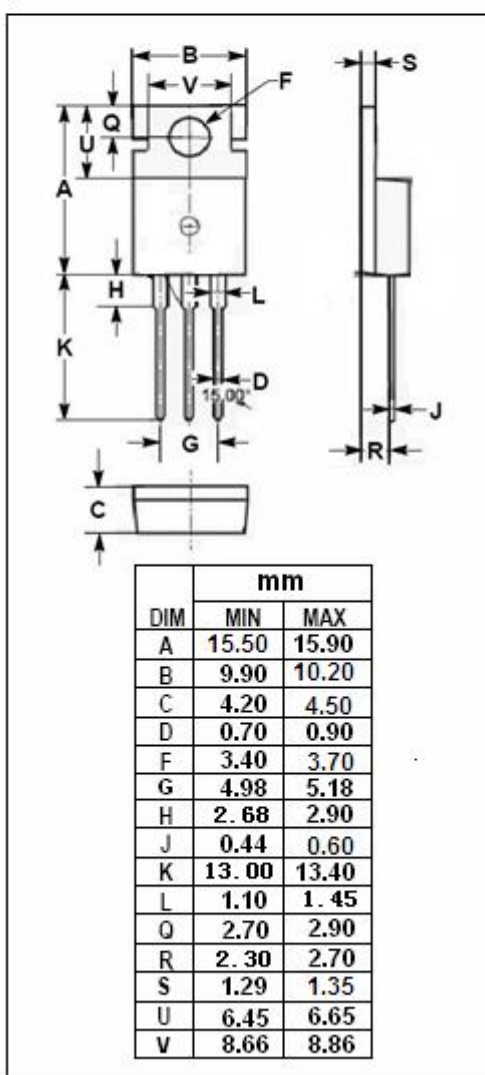
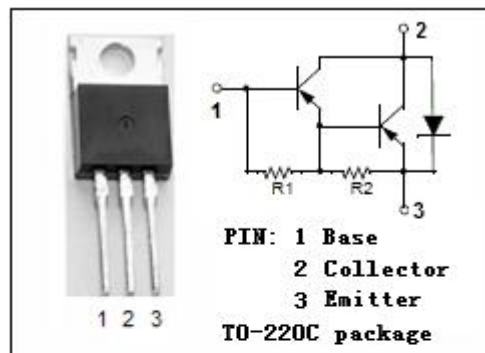
- High DC Current Gain-
: $h_{FE} = 2000(\text{Min}) @ I_C = -5A$
- Wide Area of Safe Operation
- Low Collector-Emitter Saturation Voltage-
: $V_{CE(sat)} = -1.5V(\text{Max}) @ I_C = -5A$
- Complement to Type 2SD1192

APPLICATIONS

- Designed for motor drivers, printer hammer drivers, relay drivers, voltage regulator control applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-70	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-10	A
I_{CM}	Collector Current-Peak	-15	A
P_C	Collector Power Dissipation $T_C = 25^\circ\text{C}$	40	W
	Collector Power Dissipation $T_a = 25^\circ\text{C}$	1.75	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



SPTECH Silicon PNP Darlington Power Transistor**2SB882****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA, R _{BE} = ∞	-60			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -5mA, I _E = 0	-70			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -5A, I _B = -10mA			-1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -5A, I _B = -10mA			-2.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -40V, I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-5	mA
h _{FE}	DC Current Gain	I _C = -5A; V _{CE} = -2V	2000			
f _T	Current-Gain—Bandwidth Product	I _C = -5A; V _{CE} = -5V		20		MHz

Switching times

t _{on}	Turn-on Time	R _L = 4 Ω, V _{CC} ≈ -20V I _C = -5A; I _{B1} = -I _{B2} = -10mA		0.5		μ s
t _{stg}	Storage Time			1.5		μ s
t _f	Fall Time			1.7		μ s